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Doping effect on thermoelectric properties of MoS_2

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We systematically study the potential of layered MoS_2 as a promising thermoelectric material for the first time, based on Boltzmann transport theory and first-principles calculations. Anisotropic thermoelectric transport property are investigated and compared with experimental data. A good agreement between our calculated temperature-dependent thermopower and available experimental data is obtained. We then discuss the temperature and doping level dependent thermopower, electrical conductivity, power factor (PF) and ultimately figure of merit (ZT) coefficient along in-plane and cross-plane directions. MoS_2 has a vanishingly small anisotropy of thermopower but a big anisotropy of electrical and thermal transport properties in the optimal doping region. A clear preference for thermoelectric transport under electron doping, as well as for the cross-plane transport direction is found. Our study demonstrates that it is essential to improve the thermoelectric performance of MoS_2 by reducing thermal conductivity through restacking exfoliated layers, or by electron doping through substituting at S site.

I. INTRODUCTION

Thermoelectrics play a key role for power generation and refrigeration[1–3]. Chalcogenide composite materials, such as Bi_2Te_3, PbTe and others[4–10], have attracted much research interest for decades because of their high performance on thermoelectric conversion. Transition-metal dichalcogenide MoS_2, one prototype material in chalcogenide family, has distinctive electronic, mechanical, catalytic and tribological properties[11–20]. Recent research on its optical properties[21] and lattice dynamics[22,23] has aroused renewed interest but its potential thermoelectric capability has barely been studied. Nevertheless, the lowest thermal conductivity obtained experimentally in a MoS_2-related structure[24], together with an unusually large thermopower[25–27] found in MoS_2, may render it a potential candidate for thermoelectric application.

Unfortunately, available experimental data concerning the thermoelectric transport properties of MoS_2 are quite scarce and fragmentary in literature, and no theoretical studies have thus far been found. The most significant experimental work was performed by Mansfield and Salam[27] and Thakurta et. al.[25], who studied temperature dependence of the electrical transport properties including thermopower S and electrical conductivity σ at only three samples with low dopings, but failed to investigate on the thermal-related properties. Kim et. al.[28] merely worked on the thermal conductivity κ. Based on these incomplete experimental data, it is difficult to calculate the figure of merit ZT which is crucial to evaluate thermoelectric conversion capability. Moreover, available extrinsic carrier concentrations in MoS_2 single crystals were quite low. It remains a big challenge to obtain a wide doping region in experiment but nonetheless is essential to tuning the carrier concentration appropriate for an optimum ZT.

In this letter, we study theoretically the thermoelectric transport properties of MoS_2 over a wide range of doping level (from 10^{15} to 10^{20} cm^{-3}) and focus on their directional anisotropies. We have the following findings: (1) Thermopower is attainable more than 200 μV/K over a wide range of dopings and directional thermopower anisotropy vanishes between in-plane and cross-plane thermopowers for doping level above 10^{17} cm^{-3}. (2) Anisotropic electronic scattering time exists between in-plane and cross-plane directions, which accounts for two orders of magnitude difference between σ_{xx} and σ_{zz}. (3) A clear preference for thermoelectric transport under electron doping, as well as for the cross-plane transport direction is found. (4) Heavy doping is essential for an optimal thermoelectric performance, the figure of merit ZT reaches 0.006 at 700K and 4×10^{19} cm^{-3}. (5) ZT can be further optimized by reducing cross-plane thermal conductivity through random re-stacking of exfoliated layers.

II. METHODOLOGY

The band structure of MoS_2 is calculated by using the general potential linearized augmented plane-wave(LAPW) method as implemented in the WIEN2K package[29]. The electronic exchange-correlation is described within the generalized gradient approximation (GGA) of Perdew-Burke-Ernzerhof(PBE) flavor[30]. We use 5000 k points in the full Brillouin zone(BZ) to achieve a self-consistency accuracy better than 1 meV/atom. MoS_2 has P_{63}/mmc space group symmetry and consists of a hexagonal plane of Mo atoms sandwiched by two hexagonal planes of S atoms. The unit cell contains two alternating and weakly van-der-Waals-bonded layers with an AB stacking along c axis. The experimental lattice parameters[31] (a = 3.16$\mathring{A}$, c = 12.295$\mathring{A}$) are used here.

An improved band gap is essential for calculating

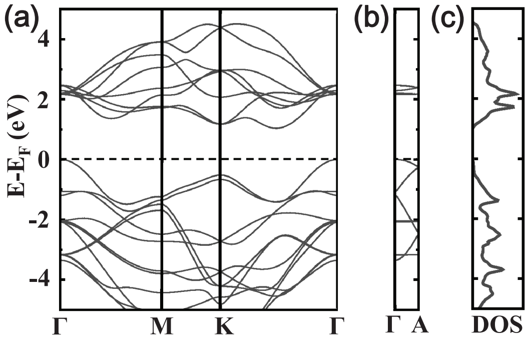

FIG. 1. (Color online) EV-GGA electronic band structure of MoS_2 along high-symmetry lines (a) Γ-M-K-Γ in plane and (b) Γ-A across plane in the hexagonal Brillouin zone (BZ). The valence-band edge is set as zero and marked with a dashed line. Electronic density of states in (c) shows a comparatively higher value at the conduction band edge than at the valence band edge.

transport quantities, so the Engel-Vosko GGA (EV-GGA) formalism[32] is applied to calculate the band gap more accurately. In Fig. 1, we present our calculated band structure and density of states of MoS_2. The in-plane and cross-plane band structure are considered separately in Fig. 1(a, b). In Fig. 1(a), an indirect gap of 1.04 eV is obtained between top of valence band at Γ and bottom of conduction band at one k point from K to Γ. A similar band structure calculated from standard PBE-GGA formalism gives an indirect gap of 0.84 eV, which agrees with reported value[33]. Compared with $\Delta_i \sim 1.20$ eV from experiment[34], it is clear that EV-GGA does improve the band gap calculation upon PBE-GGA. In contrast to the pronounced dispersive in-plane electronic bands shown in Fig. 1(a), the cross-plane bands shown in Fig. 1(b) are quite flat, showing a very weak cross-plane bonding due to Van der Waals interaction but a possibly better TE performance than in-plane bands[35]. The structural anisotropy induces an anisotropy between in-plane and cross-plane band gaps. The size of calculated cross-plane gap is found to be 2.2 eV.

III. RESULTS AND DISCUSSION

Besides the band gap anisotropy, a strong asymmetric feature of band structure between valence and conduction bands implies that the thermoelectric properties of p-type MoS_2 would be very different from that of n-type. The heavy and doubly degenerate bands near the conduction-band minimum suggest that the n-type MoS_2 would have better thermoelectric performance. In Fig. 1(c), total density of states (DOS) also shows this preference, there is a comparatively higher DOS very close to the conduction band edge than that near the valence band edge. Considering more experimental data are found for p-type in literature[25–27], we focus on hole-doped MoS_2 in this study.

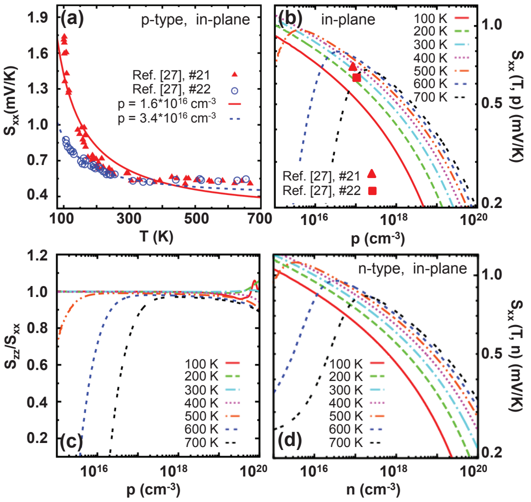

FIG. 2. (Color online) (a) Temperature dependence of calculated in-plane thermopower S_{xx} of MoS_2, compared with experimental data by Mansfield and Salam[27] at two doping levels p = 1.6 × 10^{16} (filled triangle) and 3.4 × 10^{16} (empty circle) holes per cm^3. Doping level dependence of (b) in-plane thermopower S_{xx}(p, T), (c) ratio of cross-plane S_{zz}(p, T) over in-plane S_{xx}(p, T) and (d) in-plane $S_{xx}(n, T)$ at different temperatures. The temperature ranges from 100K to 700K for some practical reason. Hole and electron doping are respectively used in (a-c) and (d). Experimental data with p = 7.6 × 10^{16} and 1.0 × 10^{17} cm^{-3} at 200K by Mansfield and Salam[27] is respectively marked by filled triangle and square in (b).

We calculate transport properties based on Boltzmann transport theory applied to the band structure. In the following part, we discuss the dependence of transport functions including S, σ, PF, κ and ultimately ZT on temperature and doping level along two directions perpendicular to each other. The electron scattering time is assumed to be independent of energy due to its good description of S(T) in a number of thermoelectric materials[6,36,37]. In this sense, no adjustable parameters are needed to calculate those thermoelectric parameters. The integration is done within the BOLTZTRAP transport code[38]. A very dense meshes up to 18000 k points in the BZ is used.

In-plane and cross-plane thermopower are firstly studied. We initially compare our calculated S with experimental data from Mansfield and Salam[27] in Fig. 2(a,b). Samples in their experiment were p-type from nature with hole carrier concentration as low as $10^{15} \sim 10^{17}$ cm^{-3}. A very good agreement is obtained. Both our calculation and available experimental data show a value of in-plane thermopower S higher than 400 μV/K and S decreases with increasing temperature as shown in Fig. 2(a). Then we extend our discussion to high doping of $10^{17} \sim 10^{20}$ cm^{-3} (corresponding to p = $10^{-5} \sim 10^{-2}$ holes per unit cell in our case) to optimize thermoelectric properties, as predicted from theory[39] and as observed in many materials[40–42] including MoS_2 that we discuss in this letter. Therefore from now on, we put more attention on this high doping region. From Fig. 2(b), the thermopower, though decreasing with doping level, takes a value of at least 200 μV/K (a ZT∼2.4 expected if Wiedemann-Franz law is assumed.) and increases with increasing temperature. To see a possible anisotropy between in-plane and cross-plane S, we show the ratio of S_{zz} over S_{xx} in Fig. 2(c). Contrary to a relatively high anisotropy of thermopower at low doping level, little difference is found at high level of doping. Not only the magnitude, but also the dependence on hole doping level and temperature are similar between S_{xx} and S_{zz}. This is different from layered conductive thermoelectric oxides such as Na_xCoO_2 and $Ca_3Co_4O_{9-\delta}$[43,44]. To confirm that n-type MoS_2 may be better, we briefly compare the data of n-type in Fig. 2(d) with p-type in Fig. 2(b). Expectedly, bigger value of thermopower of n-type MoS_2 is found.

Based on the energy-independent scattering time approximation, it is quite straightforward to get doping dependence of σ/τ at various temperature from the electronic band structure, upon which we calculate σ if τ is known. In Fig. 3(a), we show calculated σ_{xx}/τ_{xx} depending on hole doping and temperature. We find an almost temperature independence but an approximately linear doping level dependence of σ_{xx}/τ_{xx}, namely $\sigma_{xx}/\tau_{xx} \sim \mathrm{T}^0$ p. For a quadratic band dispersion in an electron-phonon approximation, $\sigma \sim \mathrm{p}^{\frac{2}{3}}\ \mathrm{T}^{-1}$ stands, this results in $\tau_{xx} \sim \mathrm{T}^{-1}\mathrm{p}^{-\frac{1}{3}}$, in consistent with the analytical treatment of carriers scattered by lattice vibrations in a semiconductor[6,45]. To calculate σ_{xx}, we need some

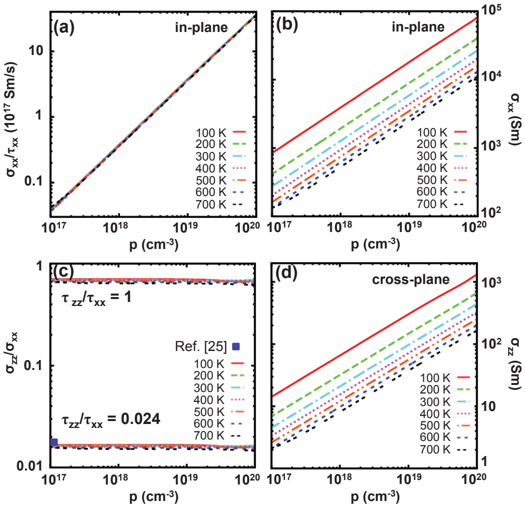

FIG. 3. (Color online) Doping level dependence of (a) in-plane σ_{xx}/τ_{xx}, (b) in-plane electrical conductivity σ_{xx}, (c) ratio of cross-plane σ_{zz}/τ_{zz} over in-plane σ_{xx}/τ_{xx} and (d) cross-plane σ_{zz}, at different temperatures. Isotropic and anisotropic electronic scattering time τ are respectively assumed in (c), for instance, $\tau_{zz}/\tau_{xx} = 1$ and 0.024 with the anisotropic one fitting well the experimental data in blue square from Thakurta et. al.[25] and thereby used to derive σ_{zz} in (d).

experimental input besides $\tau_{xx}(T, p)$. Here we use σ_{xx} = 0.16 $\Omega^{-1}cm^{-1}$ at 100 K and 1.4×10^{15} cm^{-3} doping level from the experimental data by Thakurta et. al.[25]. Our calculated σ_{xx}/τ_{xx} combined with the experimental data yields $\tau_{xx} = 2.72 \times 10^{-13}$ s at 100K and 1.4×10^{15} cm^{-3} doping level. Plugging it into our calculated σ/τ, we show $\sigma_{xx}(T, p)$ in Fig. 3(b), and power factor $\sigma_{xx}S^2_{xx}(T, p)$ in Fig. 4(a).

Electrical conductivity along c axis is also calculated and a strong anisotropy is found between the in-plane and cross-plane electronic scattering time τ. When isotropic scatter time τ is assumed, namely, $\tau_{zz}/\tau_{xx} = 1$, we obtain σ_{zz}/σ_{xx} close to unity in Fig. 3(c), which is against the reported result[25]. To fit σ_{xx}/σ_{zz} of two orders of magnitude in experiment, we use anisotropic $\tau_{zz}/\tau_{xx} = 0.024$, and therefore obtain $\tau_{zz} = 6.52\times\ 10^{-15}$ s at 100K and 1.4×10^{15} cm^{-3}. This suggests that strong anisotropic scattering effects should play a role in this system. Finally, we are able to calculate $\sigma_{zz}(T, p)$ and show it in Fig. 3(d).

With thermopower and electrical conductivity, we are able to evaluate power factor. For an optimized TE performance, peak value of PF and the corresponding doping level and temperature are more concerned here. The power factors along two perpendicular directions both have peak values spanning in a wide doping range from 10^{17} to 10^{20} cm^{-3}. From Fig. 4, the value of peak power factor is nearly constant, while its temperature increases with the hole doping level. Nearly 50-fold difference is found between in-plane and cross-plane power factors, e.g., the in-plane and cross-plane peaks σS^2 at 700 K are respectively 4.1×10^{-4} W/m/K^2 and 1.0×10^{-5} W/m/K^2. This has something to do with the anisotropic electronic scattering time τ. Unfortunately, both values are relatively lower than that expected for a good thermoelectric material. An improvement on the inter-layer electrical conductivity seems very essential to improve PF.

To optimize ZT value, the thermal conductivity κ, including electronic κ_e and lattice κ_l, is also essential. Based on the scattering time approximation previously discussed, we calculate electronic thermal conductivity (shown in Fig. 5(a,b)). At least two orders of magnitude difference between κ^e_{xx} and κ^e_{zz} are found, which is in consistent with electrical conductivity case and fits well

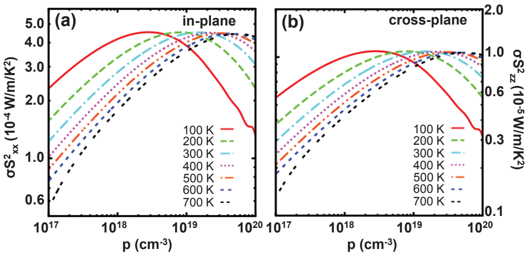

FIG. 4. (Color online) Doping level dependence of (a) power factor $\sigma_{xx}S^2_{xx}$ and (b) $\sigma_{zz}S^2_{zz}$ of p-type MoS_2 at different temperatures.

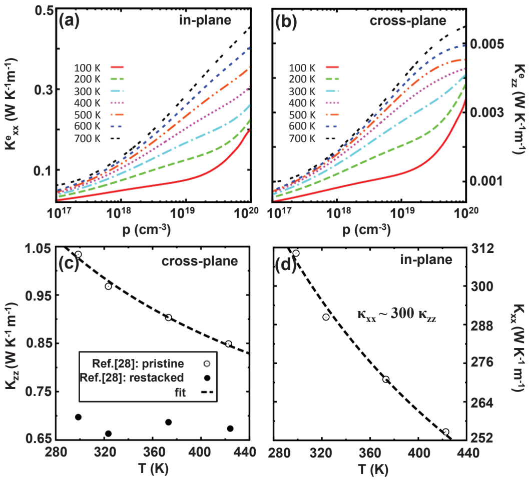

FIG. 5. (Color online) (a) In-plane electronic thermal conductivity κ^e_{xx} and (b) cross-plane κ^e_{zz} as function of doping and temperature. (c-d) Temperature dependence of thermal conductivity κ_{zz} from Kim et. al.[28] in experiment and κ_{xx} of p-type MoS_2. $\kappa_{xx} \sim 300\kappa_{zz}$ is assumed in (d). The experimental data in (c) are presented by open and solid circles for pristine and exfoliated & restacked compound, respectively, with the pristine data fitted by κ_{zz} = 183.103/T + 0.412671 in dashed line.

with the Wiedemann-Franz law. For the lattice thermal conductivity, it is not possible to calculate κ_l from electronic band structure and here we have to get it from experiment. We only find in literature the cross-plane κ_{zz} from Kim et. al.[28] and show it in Fig. 5(c). The lattice thermal conductivity dominates, for instance, total κ_{zz} = 1.00 W K^{-1} m^{-1} at 300K, which is two orders of magnitude bigger than κ^e_{zz}, let alone at lower temperature. Obviously, κ_l is approximately equal to κ. We fit the experimental data for pristine MoS_2 in Fig. 5(c) by using $\kappa = 183.103/\mathrm{T} + 0.412671$. Noticing that Umklapp process has a 1/T dependence and thermal conductivity usually gets softening with increasing temperature. No experimental data exist for in-plane lattice κ, inspired by the graphite data[46], we assumed a 300 times bigger of κ_{xx} than κ_{zz}.

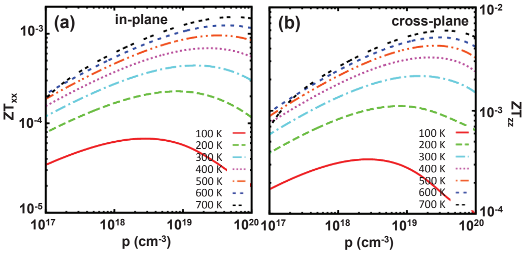

FIG. 6. (Color online) Doping level dependent (a) in-plane and (b) cross-plane figure of merit ZT of p-type MoS_2 at different temperatures.

All the data obtained above allow us to calculate ZT as function of temperature and hole doping along two directions, which is shown in Fig. 6(a,b). Optimum ZT value increases with increasing temperature, so does the corresponding optimum doping level. In-plane figure of merit falls behind cross-plane one by at least one order of magnitude, implying a better performance achieved along c-axis. However, ZT value is far below unity. To enhance the ZT along c axis, a heavier electronic/hole doping is desired and therefore upshifts its optimum working temperature. Besides doping, random stacking of two-dimensional crystalline layer to reduce the cross-plane thermal conductivity is also favorable. Kim et. al.[28] exfoliated MoS_2 films and then randomly restacked them, achieving a very low lattice κ (less than 0.7 W K^{-1} m^{-1} compared with the pristine crystal structure). But still there is some space to further reduce κ according to Chiritescu et. al.[24] where 30-fold reduction of thermal conductivity from crystal structure was obtained.

IV. CONCLUSION

To improve the thermoelectric conversion of MoS_2, we suggest to make a heavy doping. However, it seem still insufficient since power factor is behind some standard value (10^{-3} W/m/K^2). The problem lies in the poor electrical conductivity possible due to a slightly big electronegativity difference between Mo and S elements. We suggest to increase σ by substituting Se or Te for S. This has multiple advantages, e.g. to reduce the electron scattering induced by the electronegativity difference, to slow down the phonon propagation by using heavier atom, and in the meantime to realize the doping on MoS_2. More encouragingly, this may even enhance the thermopower[26]. Simply reducing further the thermal conductivity, especially the lattice thermal conductivity without affecting power factor of MoS_2, seems also possible as demonstrated on WSe_2[24] and future experiment may be needed to test this possibility. We also have to mention that our discussion is limited below 800K to avoid bipolar excitation[25], which is expected to increase thermal conductivity despite enhancing the electrical conductivity. How this bipolar excitation affects thermoelectrics above 800K also requires a further study.

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[1] Brian C. Sales, Science **295**, 1248 (2002).

[2] A. Majumdar, Science **303**, 777(2004).

[3] H. Böttner et. al., MRS Bull. **31**, 211 (2006).

[4] T. Tritt (Vol. Editor), *Recent Trends in Thermoelectric Materials Research* **vol. 69-71** (Semiconductors & Semimetals) Academic Press, San Diego (2001).

[5] J. Androulakis et. al., Phys. Rev. B **83**, 195209 (2011).

[6] K.P. Ong, D.J. Singh and P. Wu, Phys. Rev. B **83**, 115110 (2011).

[7] D. Parker and D.J. Singh, Phys. Rev. B **82**, 035204 (2010).

[8] H. Goldsmid, A. Sheard, D. Wright, Br. J. Appl. Phys. **9**, 365 (1958).

[9] R. Venkatasubramanian, E. Siivola, T. Colpitts, Nature **413**, 597 (2001).

[10] N. F. Hinsche, B. Yu. Yavorsky, I.mertig, P. Zahn, Phys. Rev. B **84**, 165214 (2011).

[11] L. Rapoport et. al., Nature(London) **387**, 791 (1997).

[12] J.M. Martin et. al., Phys. Rev. B **48**, 10583–10586 (1993).

[13] B.C. Gates, Catalytic Chemistry, Wiley, New York (1992).

[14] X. Zong et. al., J. Am. Chem. Soc. **130**, 7176 (2008).

[15] I.T. McGovern et. al., Surf. Sci. **152/153**, 1203 (1985).

[16] B. Radisavljevic et. al., Nature Nanotechnology **6**, 147 (2011).

[17] Y.B. Li, Y. Bando, and D. Golberg, Appl. Phys. Lett. **82**, 1962 (2003).

[18] E. Gourmelon et. al., Sol. Energy Mater. Sol. Cells **46**, 115 (1997).

[19] J. Chen et. al., J. Am. Chem. Soc. **123**, 11813 (2001).

[20] J. Xiao et. al., Chem. Mater. **22**, 4522-4524 (2010).

[21] K.F. Mak, C. Lee, J. Hone, J. Shan, and T.F. Heinz, Phys. Rev. Lett. **105**, 136805 (2010).

[22] C. Lee et. al., ACS Nano **4**, 2695 (2011).

[23] C. Ataca, M. Topsakal, E. Akt*ü*rk, and S. Ciraci, J. Phys. Chem. C **115**, 16354-16361 (2011).

[24] C. Chiritescu et. al., Science **315**, 351 (2007).

[25] S.R. Guha Thakurta and A.K. Dutta, J. Phys. Chem. Solids **44**, 407 (1983).

[26] M.K. Agarwal and L.T. Talele, Sol. State Comm. **59**, 549 (1986).

[27] R. Mansfield and S.A. Salam, Proc. Phys. Soc. B **66**, 377 (1953).

[28] J.-Y. Kim et. al., Bull. Korean Chem. Soc. **31**,3225 (2010).

[29] P. Blaha et. al., WIEN2k: An augmented plane wave plus local orbitals program for calculating crystal properties (TU Vienna, Vienna, 2011).

[30] J.P. Perdew, K. Burke and M. Ernzerhof, Phys. Rev. Lett. **77**, 3865 (1996).

[31] R. Coehoorn et. al., Phys. Rev. B **35**, 6195 (1987).

[32] E. Engel and S.H. Vosko, Phys. Rev. B **47**, 13164 (1993).

[33] S.W. Han et. al., Phys. Rev. B, **84**, 045409 (2011).

[34] K.K. Kam and B.A. Parkinson, J. Phys. Chem. **86**, 463 (1982).

[35] G. D. Mahan and J. Sofo, Proc. Natl. Acad. Sci. U.S.A. 93, 7436 (1996).

[36] D. Parker, M.-H. Du, and D.J. Singh, Phys. Rev. B **83**, 245111 (2011).

[37] L. Zhang and D.J. Singh, Phys. Rev. B **80**, 075117 (2009).

[38] G.K.H. Madsen, K. Schwarz, P. Blaha, and D.J. Singh, Phys. Rev. B. **68**, 125212 (2003).

[39] G.D. Mahan, "Good Thermoelectrics" in *Solid State Physics* **vol. 51**, ed. by H. Ehrenreich and F. Saepen (Academic Press, San Diego, 1998).

[40] D.M. Rowe and G. Min, J. Mater. Sci. Lett. **14**, 617-619 (1995).

[41] Y. Zhang et al., Phys. Rev. Lett. **106**, 206601 (2011).

[42] G.J. Snyder and E.S. Toberer, nature materials **7**, 105 (2008).

[43] K.P. Ong, D.J. Singh and P. Wu, Phys. Rev. Lett. **104**, 176601 (2010), K.P. Ong, J. Zhang, J.S. Tse and P. Wu, Phys. Rev. B **81**, 115120 (2010).

[44] G.D. Tang et. al., Appl. Phys. Lett. **98**, 202109 (2011).

[45] J. M. Ziman, *Principles of the theory of solids*, 2nd Ed.(Cambridge University Press, 1995)

[46] Goodfellow, *Metals, Alloys, Compounds, Ceramics, Polymers, Composites*, catalogues 1993/94, Goodfellow Metals Limited, Cambridge (1994).